

Features

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench technology

Description

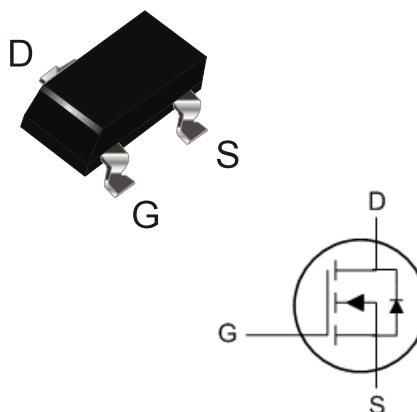
The JHT0008 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The JHT0008 meet the RoHS and Green Product requirement with full function reliability approved.

Product Summary

BVDSS	RDSON	ID
100V	310mΩ	1.2A

SOT23 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	1.2	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	1	A
I_{DM}	Pulsed Drain Current ²	5	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.067	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =1A	---	260	310	mΩ
		V _{GS} =4.5V, I _D =0.5A	---	270	320	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.5	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.2	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	5	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =1A	---	2.4	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.8	5.6	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =80V, V _{GS} =10V, I _D =1A	---	9.7	13.6	nC
Q _{gs}	Gate-Source Charge		---	1.6	2.2	
Q _{gd}	Gate-Drain Charge		---	1.7	2.4	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω I _D =1A	---	1.6	3.2	ns
T _r	Rise Time		---	19	34	
T _{d(off)}	Turn-Off Delay Time		---	13.6	27	
T _f	Fall Time		---	19	38	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	508	711	pF
C _{oss}	Output Capacitance		---	29	41	
C _{rss}	Reverse Transfer Capacitance		---	16.4	23	
Diode Characteristics						
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	1.2	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	5	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =1A, di/dt=100A/μs, T _J =25°C	---	14	---	nS
Q _{rr}	Reverse Recovery Charge		---	9.3	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

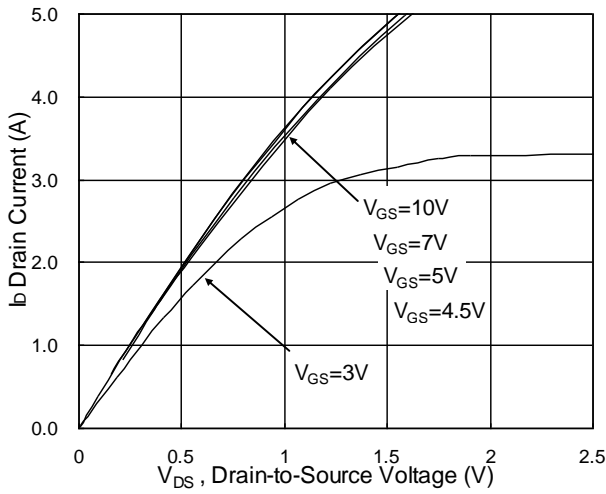


Fig.1 Typical Output Characteristics

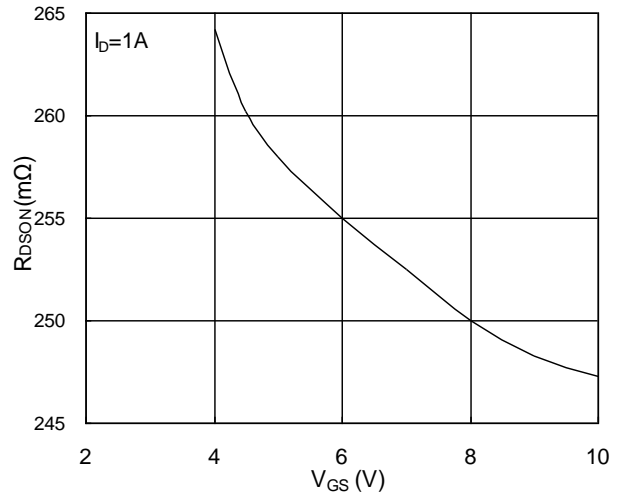


Fig.2 On-Resistance vs. Gate-Source

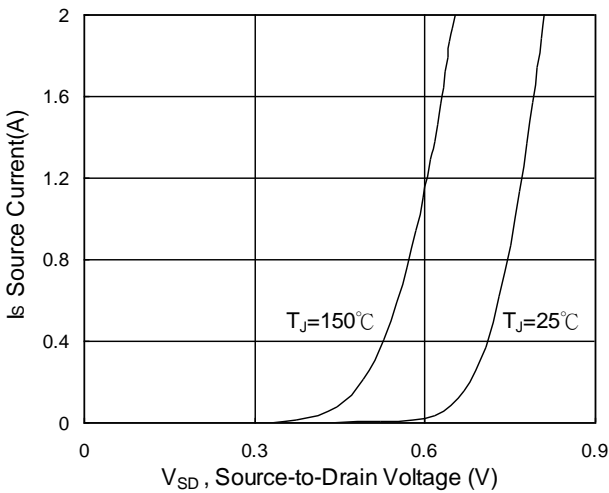


Fig.3 Forward Characteristics of Reverse

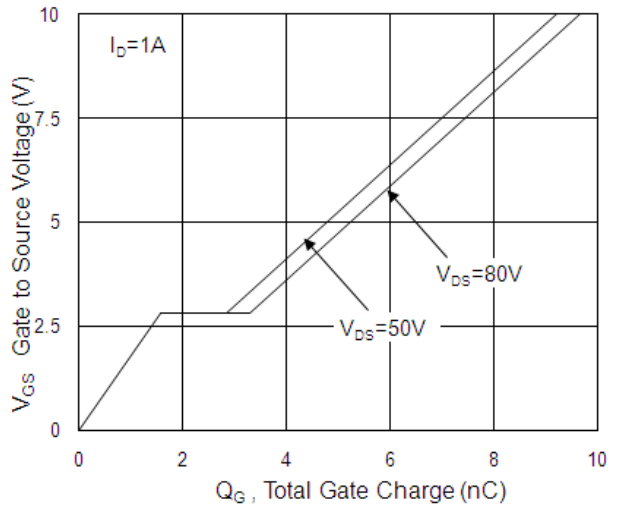


Fig.4 Gate-Charge Characteristics

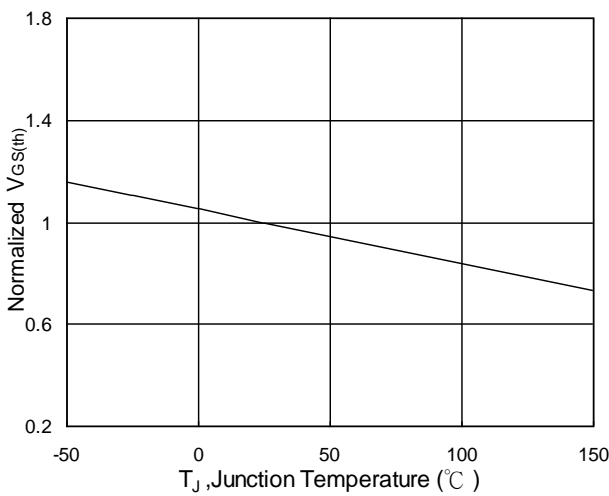


Fig.5 Normalized V_{GS(th)} vs. T_J

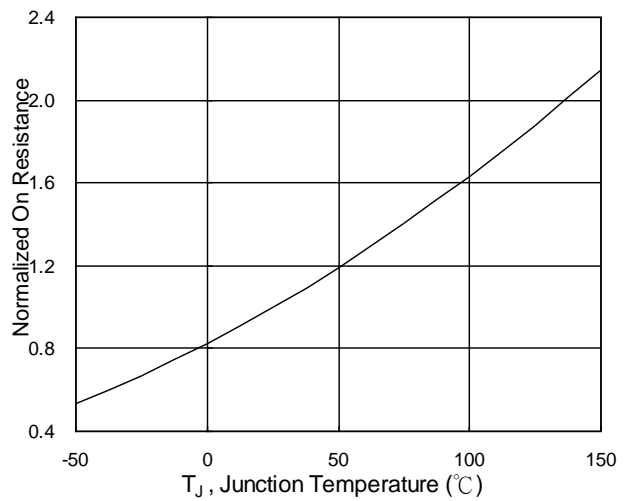


Fig.6 Normalized R_{DS(on)} vs. T_J

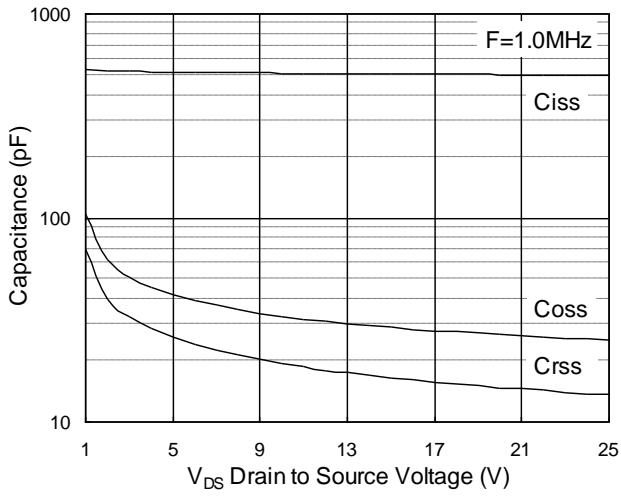


Fig.7 Capacitance

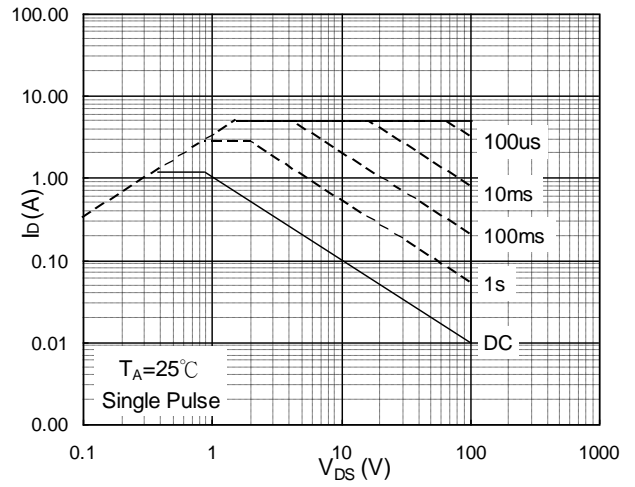


Fig.8 Safe Operating Area

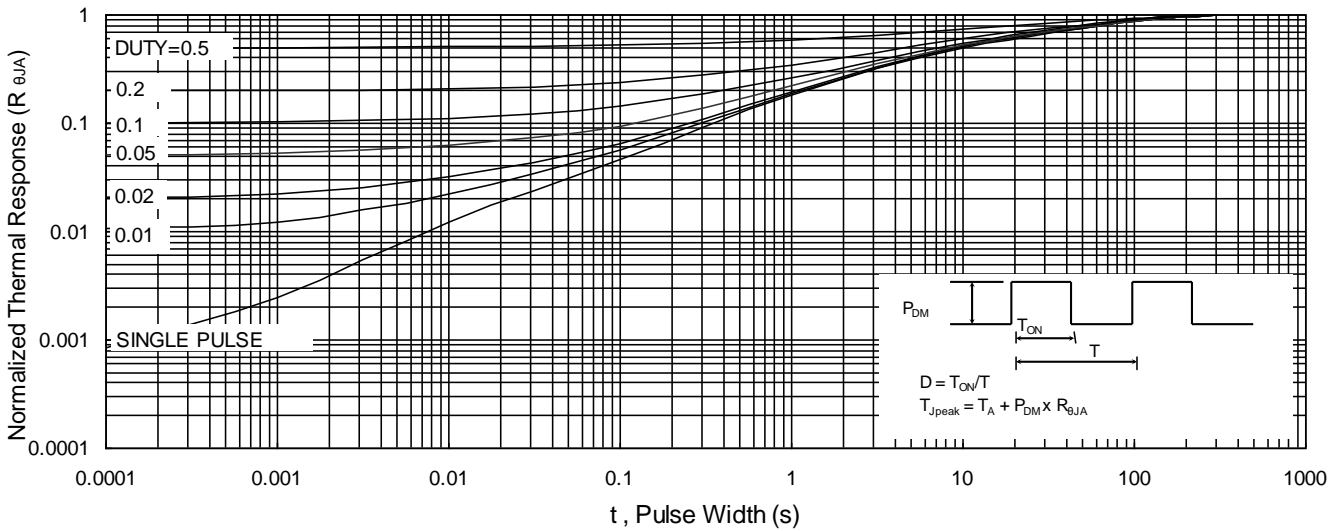


Fig.9 Normalized Maximum Transient Thermal Impedance

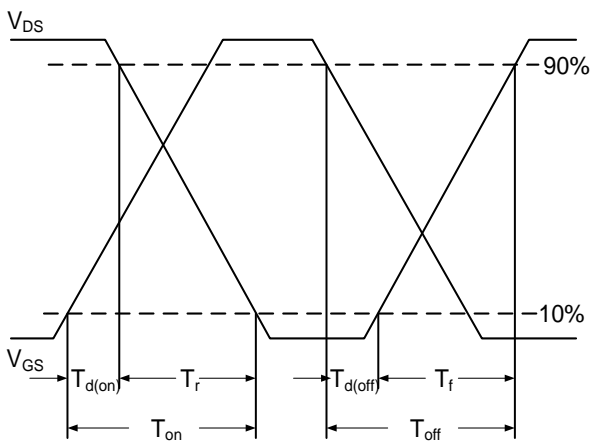


Fig.10 Switching Time Waveform

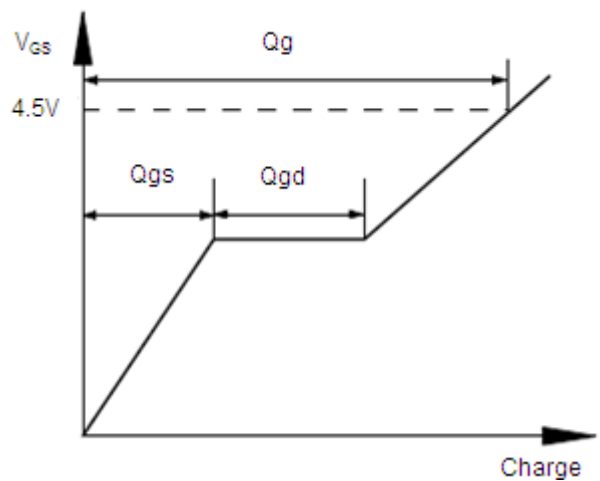
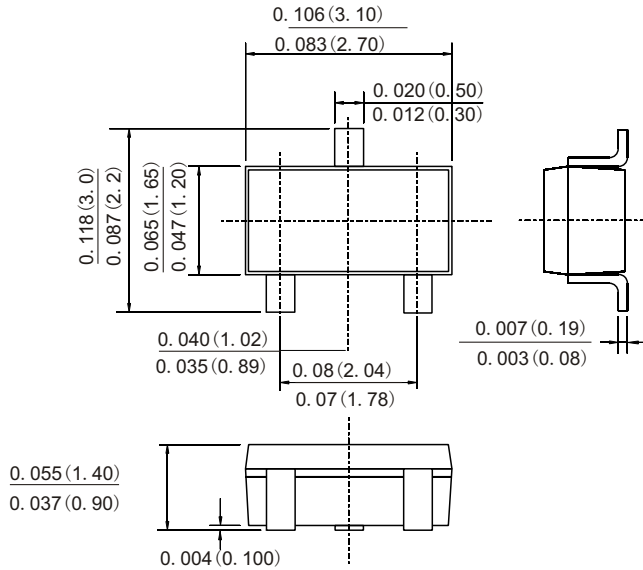


Fig.11 Gate Charge Waveform

JHT0008

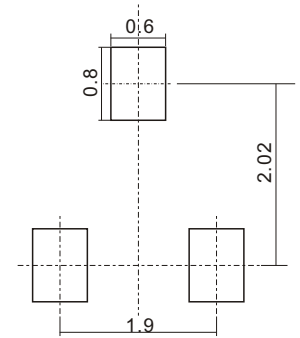
PACKAGE OUTLINE DIMENSIONS

SOT-23



Dimensions in inches and (millimeters)

Suggested Pad Layout



Dimensions in millimeters

Friendship Reminder

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